# SENSITRON

## SEMICONDUCTOR

MURC620

Technical Data Data Sheet 4857, Rev.-

# MURC620 Ultrafast Silicon Die

### **Applications:**

• Switching Power Supply • General Purpose • Free-Wheeling Diodes • Polarity Protection Diode

#### Features:

- Glass-Passivated
- Epitaxial Construction.
- Low Reverse Leakage Current
- High Surge Current Capability
- Low Forward Voltage Drop
- Fast Reverse-Recovery Behavior

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V <sub>RWM</sub>	-	200	V
Max. Average Forward	I <sub>F(AV)</sub>	50% duty cycle @T <sub>C</sub> =100°C, rectangular wave form	6.0	A
Max. Peak One Cycle Non- Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	60	A
Max. Junction Capacitance	CJ	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz, V <sub>SIG</sub> = 50mV (p-p)	75	pF
Max. Junction Temperature	TJ	-	-65 to +150	°C
Max. Storage Temperature	T <sub>stg</sub>	-	-65 to +150	°C

### **Electrical Characteristics:**

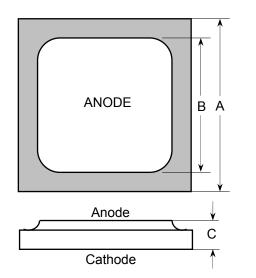
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop *	$V_{F1}$	@ 6.0A, Pulse, T <sub>J</sub> = 25 °C	1.2	V
	V <sub>F2</sub>	@ 6.0A, Pulse, T <sub>J</sub> = 100 °C	1.0	V
Max. Reverse Current *	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> T <sub>J</sub> = 25 °C	6	μA
	I <sub>R2</sub>	@V <sub>R</sub> = 0.8V <sub>R</sub> T <sub>J</sub> = 100 °C	60	μA
Max Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =0.5A, I <sub>R</sub> =1.0A, I <sub>REC</sub> =0.25A	25	nS
Max Reverse Recovery Time	t <sub>rr</sub>	l <sub>F</sub> =6A, di/dt=200A/µs	35	nS

\* Pulse Width < 300µs, Duty Cycle <2%

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## Dimensions in inches (mm)



Top side metalization: AI - 25 kÅ minimum or Ti/Ni/Ag - 30 kÅ minimum

Bottom side metalization: Ti/Ni/Ag - 30 kÅ minimum. Bottom side is cathode, top side is anode.

Die type	Area (mil <sup>2</sup> )	Dimension A <sup>(1)</sup>	Dimension B <sup>(1)</sup>	Dimension C <sup>(2)</sup>
		Inch (millimeter)	Inch (millimeter)	Inch (millimeter)
Si p-n die	85 x 85	0.085 (2.159)	0.069 (1.753)	0.009 (0.229)

<sup>(1)</sup> Tolerance is ± 0.003" (0.076 mm) <sup>(2)</sup> Tolerance is ± 0.001" (0.025 mm)

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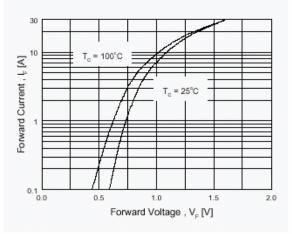
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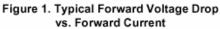
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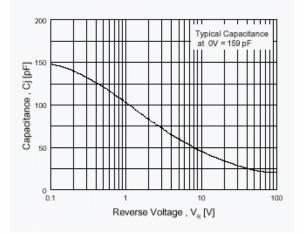


Figure 3. Typical Junction Capacitance

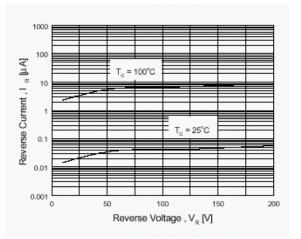
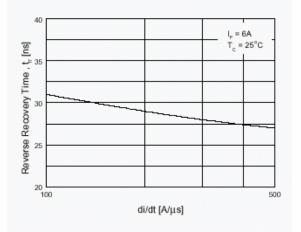
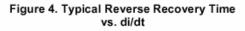


Figure 2. Typical Reverse Current vs. Reverse Voltage





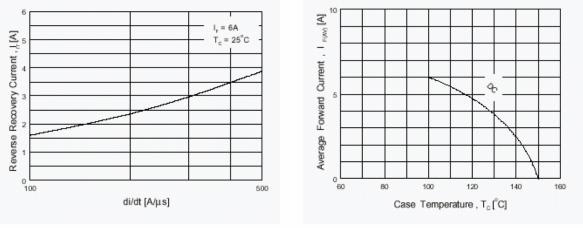


Figure 5. Typical Reverse Recovery Current vs. di/dt

Figure 6. Forward Current Derating Curve